



PJQ4411P

20V P-Channel Enhancement Mode MOSFET

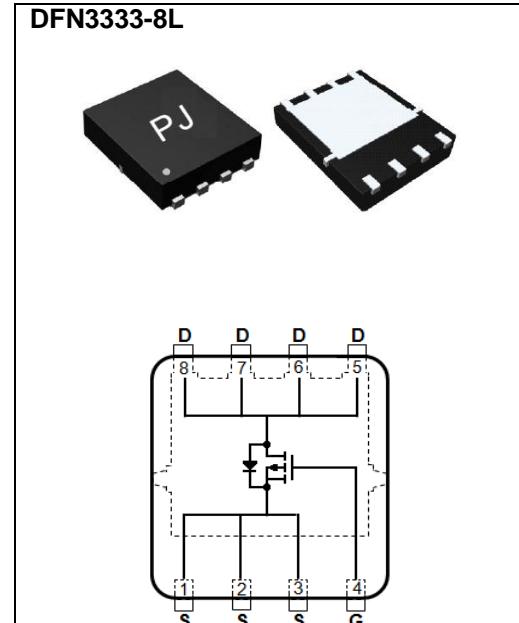
Voltage -20 V Current -60 A

Features

- $R_{DS(ON)}$, $V_{GS} @ -4.5V, I_D @ -8A < 8m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ -2.5V, I_D @ -5A < 11m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ -1.8V, I_D @ -3A < 16m\Omega$
- Advanced Trench Process Technology.
- High density cell design for ultra-low on-resistance.
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.001 ounces, 0.03 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	-60	A
		-38	
Pulsed Drain Current ^(Note 1,4)	I_{DM}	-200	
Power Dissipation	P_D	60	W
		24	
Continuous Drain Current	I_D	-13	A
		-10	
Power Dissipation	P_D	2.0	W
Power Dissipation		1.3	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ C$
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{\theta JC}$	$^\circ C/W$
	Junction to Ambient	$R_{\theta JA}$	

- Limited only by Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.3	-0.6	-1.0	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-8A$	-	6	8	$m\Omega$
		$V_{GS}=-2.5V, I_D=-5A$	-	8	11	
		$V_{GS}=-1.8V, I_D=-3A$	-	11	16	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
Dynamic <small>(Note 6)</small>						
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-5A,$ $V_{GS}=-4.5V$ <small>(Note 1,2)</small>	-	46.8	-	nC
Gate-Source Charge	Q_{gs}		-	7.4	-	
Gate-Drain Charge	Q_{gd}		-	11.1	-	
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $f=1.0MHz$	-	4659	-	pF
Output Capacitance	C_{oss}		-	539	-	
Reverse Transfer Capacitance	C_{rss}		-	440	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-10V, I_D=-1A,$ $V_{GS}=-4.5V, R_G=25\Omega$ <small>(Note 1,2)</small>	-	42	-	ns
Turn-On Rise Time	t_r		-	78	-	
Turn-Off Delay Time	$t_{d(off)}$		-	510	-	
Turn-Off Fall Time	t_f		-	265	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_s	---	-	-	-60	A
Diode Forward Voltage	V_{SD}	$I_s=-1A, V_{GS}=0V$	-	-0.7	-1	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^\circ C$.
4. The maximum current rating is package limited
5. $R_{Theta A}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
6. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

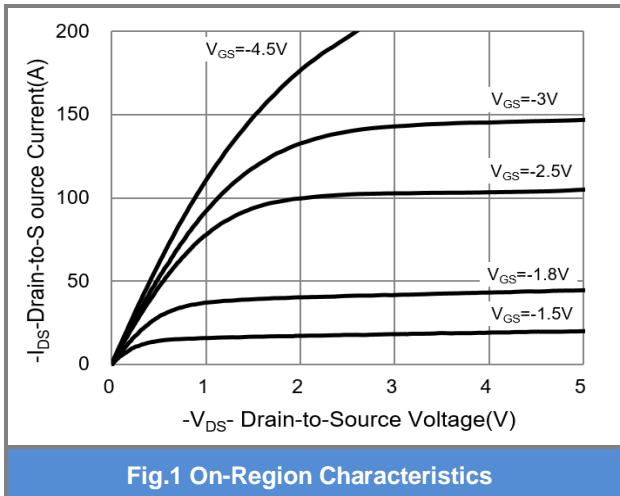


Fig.1 On-Region Characteristics

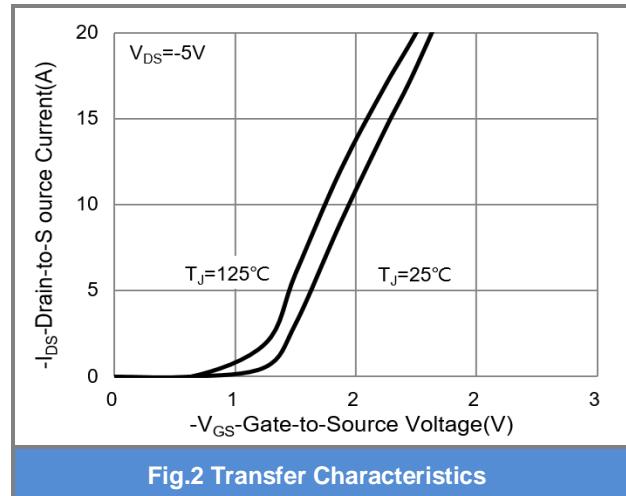


Fig.2 Transfer Characteristics

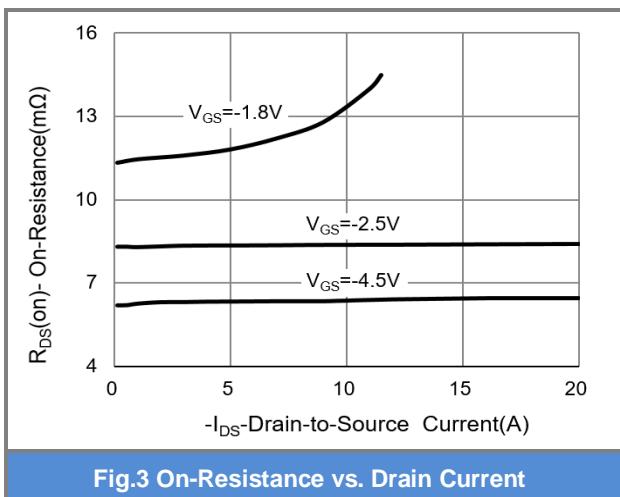


Fig.3 On-Resistance vs. Drain Current

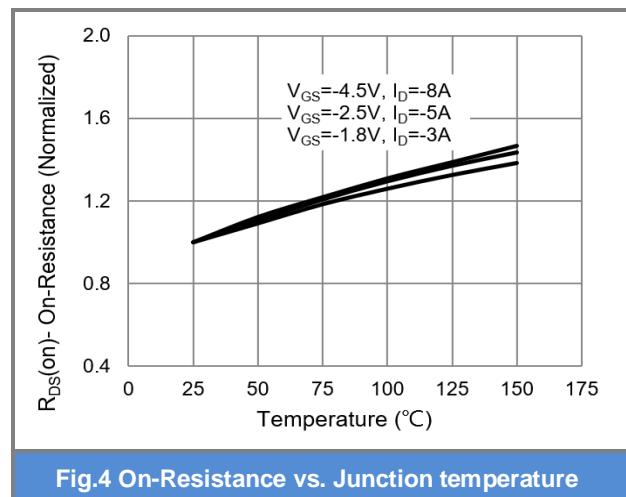


Fig.4 On-Resistance vs. Junction temperature

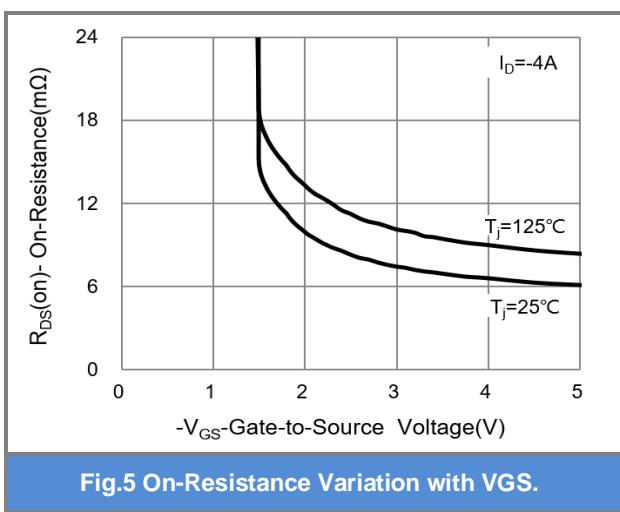


Fig.5 On-Resistance Variation with VGS.

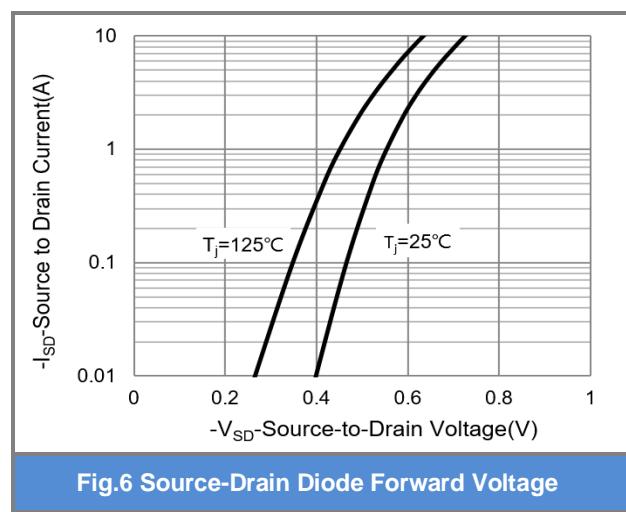


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

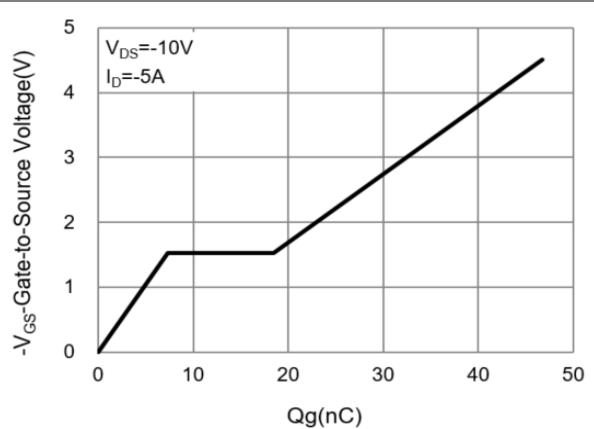


Fig.7 Gate-Charge Characteristics

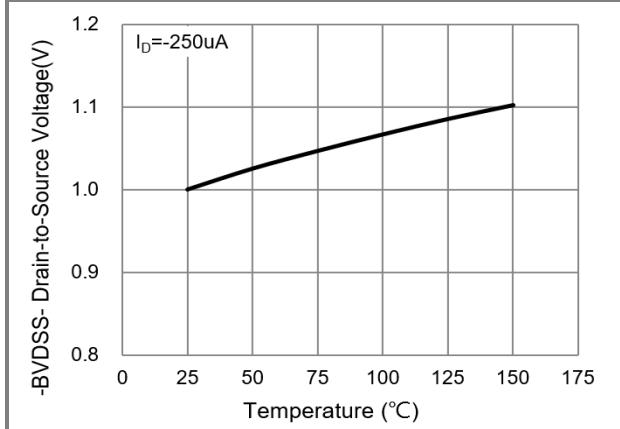


Fig.8 Breakdown Voltage Variation vs. Temperature.

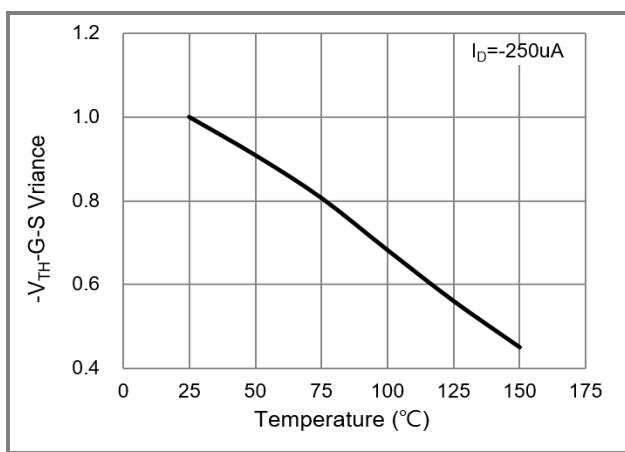


Fig.9 Threshold Voltage Variation with Temperature

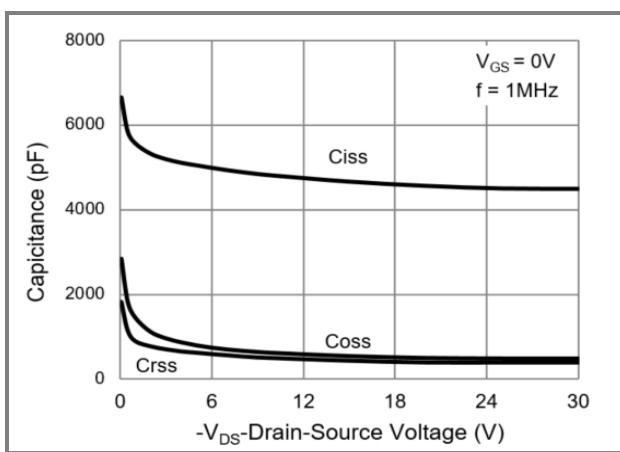


Fig.10 Capacitance vs. Drain-Source Voltage

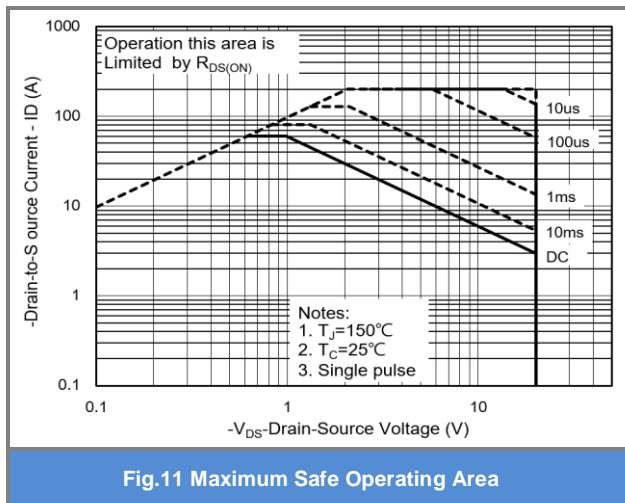


Fig.11 Maximum Safe Operating Area



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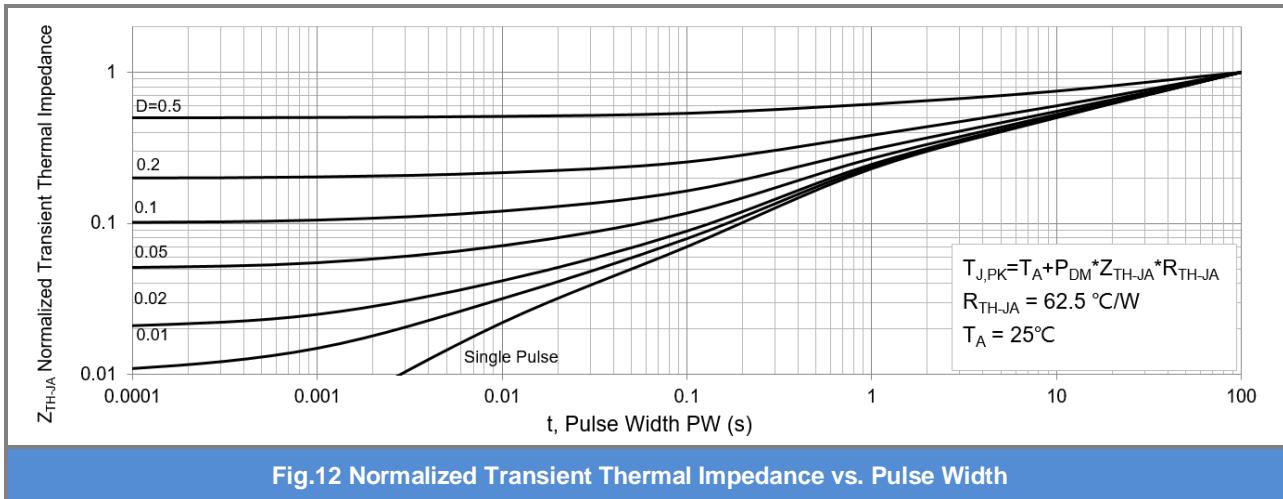


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

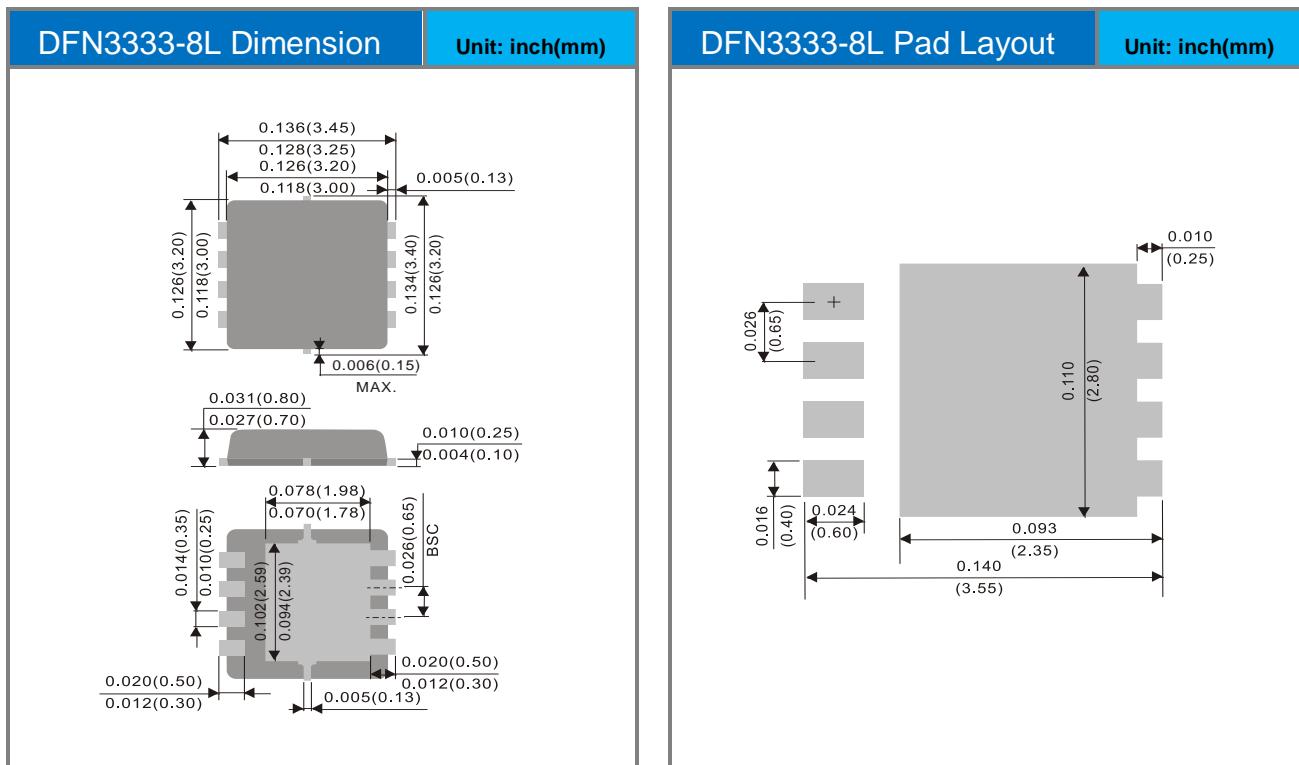


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Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ4411P_R2_00001	DFN3333-8L	5K pcs / 13" reel	4411	Halogen free

Packaging Information & Mounting Pad Layout





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